

# MICRO ELECTRONICS

## BF491,2,3

PNP SILICON  
HIGH VOLTAGE  
TRANSISTORS

BF491, BF492, BF493 are PNP silicon planar transistors designed for high voltage video amplifiers in television receivers requiring high breakdown voltage and low capacitance.



EBC

### ABSOLUTE MAXIMUM RATINGS

|  |                | BF491 | BF492                      | BF493 |
|--|----------------|-------|----------------------------|-------|
| Collector-Emitter Voltage  | $V_{CEO}$      | 200V  | 250V                       | 300V  |
| Collector-Base Voltage   | $V_{CBO}$      | 200V  | 250V                       | 300V  |
| Emitter-Base Voltage   | $V_{EBO}$      | 6V    | 8V                         | 8V    |
| Collector Current  | $I_C$          |       | 500mA                      |       |
| Total Device Dissipation @ $T_A=25^\circ\text{C}$<br>Derate Above $25^\circ\text{C}$ | $P_D$          |       | 625mW                      |       |
| Total Device Dissipation @ $T_C=25^\circ\text{C}$<br>Derate Above $25^\circ\text{C}$ | $P_D$          |       | 1.2mW/ $^\circ\text{C}$    |       |
| Operating & Storage Junction Temperature Range                                       | $T_j, T_{stg}$ |       | 1.5W                       |       |
|  |                |       | 12mW/ $^\circ\text{C}$     |       |
|  |                |       | -55 to $150^\circ\text{C}$ |       |

### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

| PARAMETER                            | SYMBOL        | BF491 |     | BF492 |     | BF493 |     | UNIT          | TEST CONDITION                                  |
|--------------------------------------|---------------|-------|-----|-------|-----|-------|-----|---------------|---|
|                                      |               | MIN   | MAX | MIN   | MAX | MIN   | MAX |               |   |
| Collector-Base Breakdown Voltage     | $V_{CBO}$     | 200   | 250 | 300   |     |       |     | V             | $I_C=0.1\text{mA}$ $I_E=0$                      |
| Collector-Emitter Breakdown Voltage  | $V_{CEO}^*$   | 200   | 250 | 300   |     |       |     | V             | $I_C=1\text{mA}$ $I_B=C$                        |
| Emitter-Base Breakdown Voltage       | $V_{EBO}$     | 6     | 8   | 8     |     |       |     | V             | $I_E=0.1\text{mA}$ $I_C=C$                      |
| Collector Cutoff Current             | $I_{CBO}$     | 0.1   |     |       |     |       |     | $\mu\text{A}$ | $V_{CB}=160\text{V}$ $I_E=C$                    |
|                                      |               |       |     | 0.1   | 0.1 |       |     | $\mu\text{A}$ | $V_{CB}=200\text{V}$ $I_E=C$                    |
| Emitter Cutoff Current               | $I_{EBO}$     | 0.1   |     |       |     |       |     | $\mu\text{A}$ | $V_{EB}=4\text{V}$ $I_C=C$                      |
|                                      |               |       |     | 0.1   | 0.1 |       |     | $\mu\text{A}$ | $V_{EB}=6\text{V}$ $I_C=C$                      |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ |       | 2   | 2     |     | 2     |     | V             | $I_C=20\text{mA}$ $I_B=2\text{mA}$              |
| Base-Emitter Saturation Voltage      | $V_{BE(sat)}$ |       | 2   | 2     |     | 2     |     | V             | $I_C=20\text{mA}$ $I_B=2\text{mA}$              |
| D.C. Current Gain                    | $H_{FE}$      | 25    | 25  | 25    |     |       |     |               | $I_C=1\text{mA}$ $V_{CE}=10\text{V}$            |
|                                      |               | 40    | 40  | 40    |     |       |     |               | $I_C=10\text{mA}$ $V_{CE}=10\text{V}$           |
| Current Gain-Bandwidth Product       | $f_T$         | 50    | 50  | 50    |     |       |     | MHz           | $I_C=10\text{mA}$ $V_{CE}=20\text{V}$           |
| Feedback Capacitance                 | $C_{re}$      | 2     | 2   | 2     |     |       |     | pF            | $V_{CB}=100\text{V}$ $I_E=0$<br>$f=1\text{MHz}$ |

\*Pulse Test : Pulse Width  $\leq 300\mu\text{S}$ , Duty Cycle  $\leq 2\%$ .

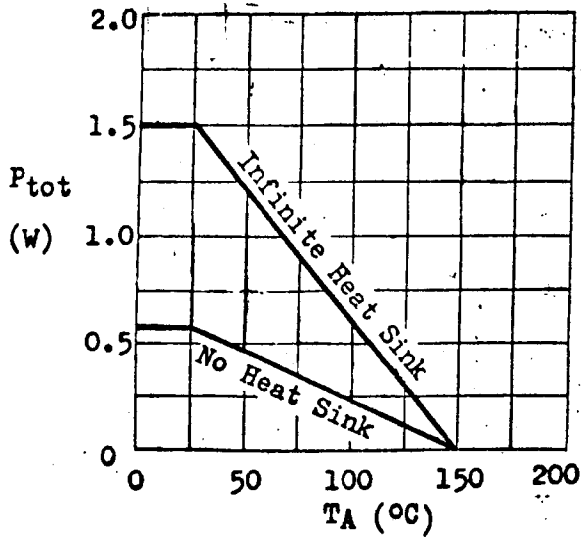


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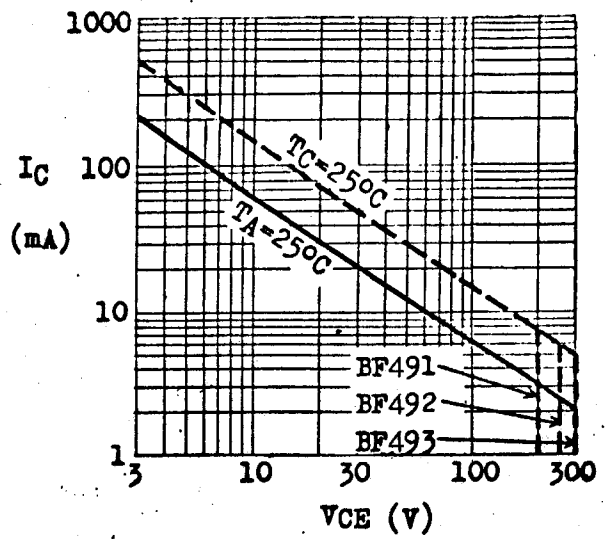
38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro HX.

P.O. Box 49477, Kwun Tong. Tel: 3-430181-6 3-893363, 3-892423, 3-898221 FAX: 3-410321

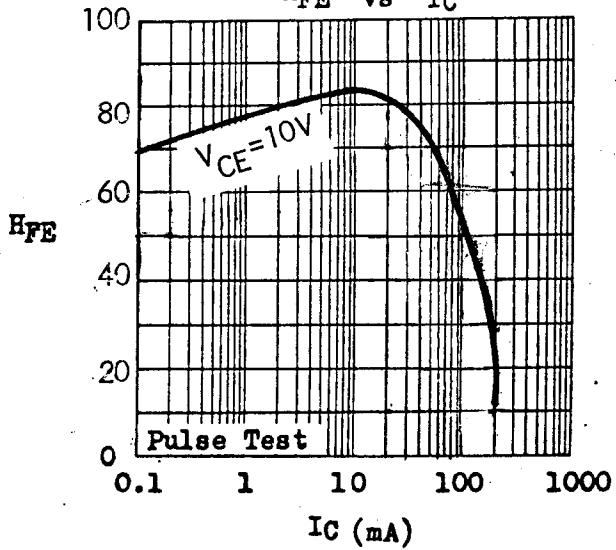
P<sub>tot</sub> vs T<sub>A</sub>



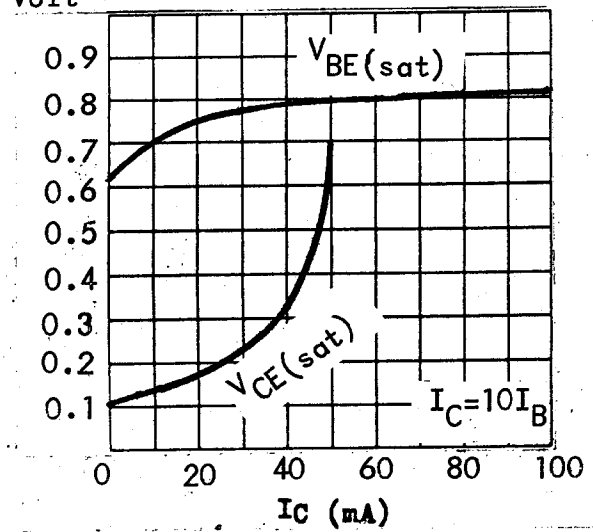
SAFE OPERATING AREA (D.C.)



H<sub>FE</sub> vs I<sub>C</sub>



V<sub>BE(sat)</sub> & V<sub>CE(sat)</sub> vs I<sub>C</sub>



f<sub>T</sub> vs I<sub>C</sub>

